



February 9, 2004

To: Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572  
28 Davis Avenue  
Poughkeepsie, N.Y. 12603

Subject: | Serial No. 10/730,778 12/09/03 |  
| Yee-Chia Yeo et al.

COMPLEMENTARY METAL OXIDE SEMI-  
CONDUCTOR TRANSISTOR TECHNOLOGY  
USING SELECTIVE EPITAXY OF A  
STRAINED SILICON GERMANIUM LAYER

#### INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation  
In An Application.

The following Patents and/or Publications are submitted to  
comply with the duty of disclosure under CFR 1.97-1.99 and  
37 CFR 1.56.

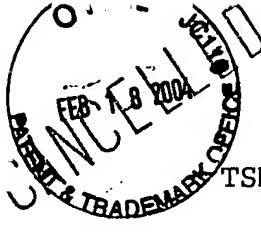
#### CERTIFICATE OF MAILING

I hereby certify that this correspondence is being  
deposited with the United States Postal Service as first class  
mail in an envelope addressed to: Commissioner for Patents,  
P.O. Box 1450, Alexandria, VA 22313-1450, on February 17, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

 2/17/04



U.S. Patent 5,534,713 to Ismail et al., "Complementary Metal-Oxide Semiconductor Transistor Logic Using Strained Si/SiGe Heterostructure Layers," describes the use of thick buffer layers, used with a SiGe layer.

U.S. Patent 5,019,882 to Solomon et al., "Germanium Channel Silicon MOSFET," discloses a Ge channel Si MOSFET process.

U.S. Patent 6,004,137 to Crabbe et al., "Method of Making Graded Channel Effect Transistor," discloses a SixGe1-x graded channel effect Tx.

U.S. Patent 5,985,703 to Banerjee, "Method of Making Thin Film Transistors," discloses a Tx using SixGe1-x layers.

U.S. Patent 5,241,197 to Murakami et al., "Transistor Provided with Strained Germanium Layer," discloses FET's with SixGe1-x layers.

U.S. Patent 5,981,345 to Ryum et al., "FI/SiGe MOSFET and Method for Fabricating the Same," discloses a SixGe1-x channel.

Sincerely,

Stephen B. Ackerman,  
Reg. No. 37761

**EXAMINER:** Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.